2SC5390

Silicon NPN Epitaxial High Frequency Amplifier

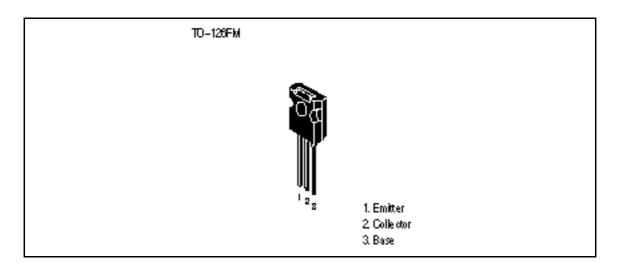
HITACHI

ADE-208-492 (Z) 1st. Edition December. 1996

Features

- Excellent high frequency characteristics $f_{T} = 1.4 GHz \; (typ.) \label{eq:ft}$
- Low output capacitance $C_{ob} = 2.4 \text{ pF (typ.)}$
- Isolated package TO-126FM

Outline





2SC5390

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

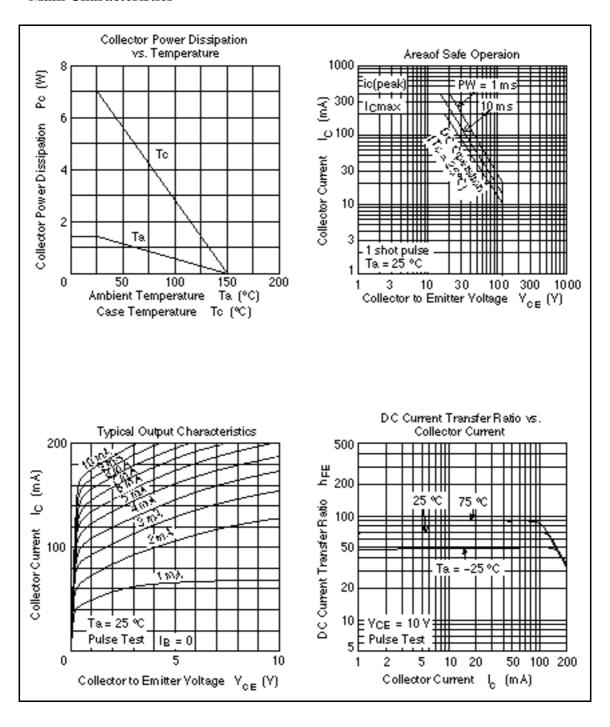
Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	110	V	
Collector to emitter voltage	V _{CEO} 110		V	
Emitter to base voltage	V_{EBO}	3	V	
Collector current	I _c	200	mA	
Collector peak current	i _{c(peak)}	400	mA	
Collector power dissipation	P _c	1.4	W	
Collector power dissipation	P _c *1	7	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	−55 to +150	°C	

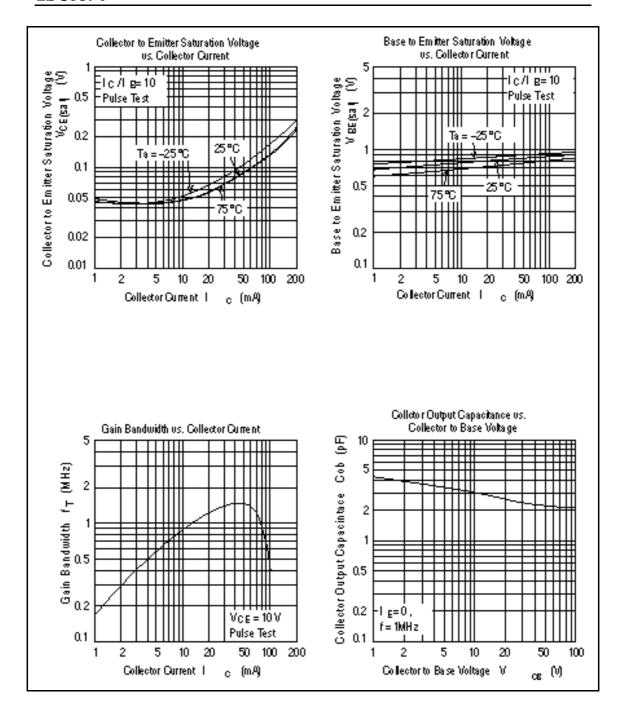
Note: 1. Value at Tc = 25°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	110	_	_	V	$I_{\rm C} = 10 \text{\'E} \text{ A}, I_{\rm E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	110	_	_	V	$I_{C} = 1mA, R_{BE} =$
Collector cutoff current	I _{CBO}	_	_	10	μΑ	$V_{CB} = 100V, I_{E} = 0$
Emitter cutoff current	I _{EBO}	_	_	10	μΑ	$V_{EB} = 3V, I_{C} = 0$
DC current transfer ratio	h _{FE}	30	_	100		$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{mA}$
Base to emitter voltage	V_{BE}	_	_	1	V	$V_{CE} = 10 \text{ V}, I_{C} = 10 \text{mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	1	V	$I_{C} = 200 \text{mA}, I_{B} = 20 \text{mA}$
Gain bandwidth product	f _T	1.0	1.4	_	GHz	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{mA}$
Collector Output capacitance	C _{ob}	_	2.4	3.5	pF	$V_{CB} = 30V$, $I_{E} = 0$ f = 1MHz

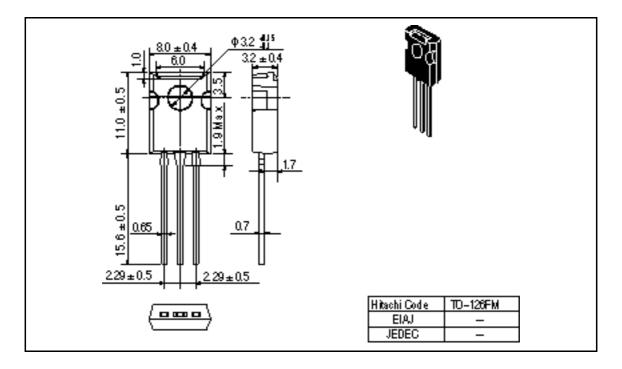
Main Characteristics





Package Dimentions

Unit: mm



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